Central™
Semiconductor Corp.

PROCESS CP792

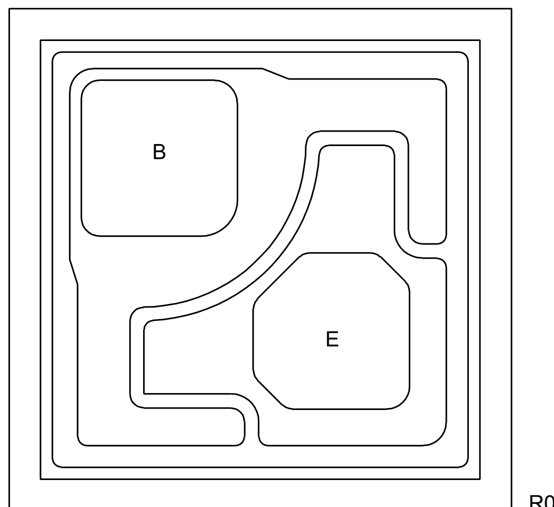
Small Signal Transistor

PNP - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER
93,826

PRINCIPAL DEVICE TYPES
2N3906
CMKT3906
CMLT3906E
CMPT3906
CMPT3906E
CMST3906
CXT3906
CZT3906

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R0 (06 -April 2004)